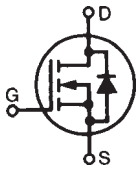
Trench Gate Power MOSFET

IXTQ 80N28T

V_{DSS} = 280 V
I_{D25} = 80 A
$R_{DS(on)}$ = 49 mΩ

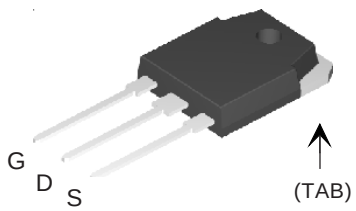
N-Channel Enhancement Mode

For Plasma Display Applications



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	280	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ	280	V
V_{GSM}		±30	V
I_{D25}	T_C = 25°C	80	A
I_{DRMS}	External lead current limit	75	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	240	A
dv/dt	$I_S \le I_{DM}$, di/dt ≤ 100 A/µs, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$, R_G = 4 Ω	5	V/ns
P_D	T_C = 25°C	500	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s	300	°C
M_d	Mounting torque (TO-3P)	1.13/10	Nm/lb.in.
Weight		5.5	g

TO-3P (IXTQ)



G = Gate D = Drain
S = Source TAB = Drain

Features

- Trench gate construction for low $R_{DS(on)}$
- International standard package
- Low package inductance
  - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

Symbol (T_J = 25°C, unless otherwise specified)	Test Conditions	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0 V, I_D =1mA	280	300		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 1mA	3.0		5.0	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0			±200	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0 V			1	µA
	T_J = 125°C			200	µA
$R_{DS(on)}$	V_{GS} = 10 V, $I_D = 0.5\ I_{D25}$, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %		42	49	mΩ

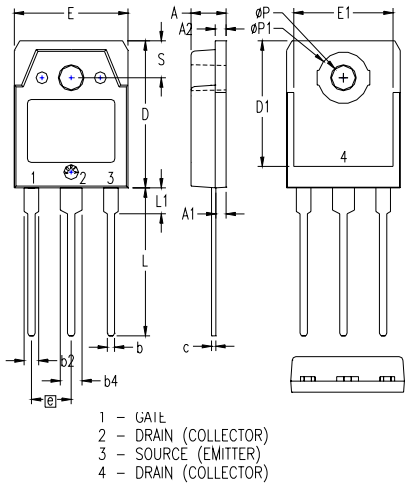
© 2006 IXYS All rights reserved

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) Min.	Typ.	Max.	
g_{fs}	V_{DS}= 10 V; I_D = 0.5 I_{D25}, pulse test	40	60		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		5000		pF
C_{oss}			510		pF
C_{rss}			29		pF
$t_{d(on)}$	V_{GS} = 15 V, V_{DS} =220 V, I_D = 40A R_G = 5 Ω (External)		37		ns
t_r			47		ns
$t_{d(off)}$			80		ns
t_f			50		ns
$Q_{g(on)}$	V_{GS}= 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}		115		nC
Q_{gs}			40		nC
Q_{gd}			37		nC
R_{thJC}				0.25	K/W
R_{thCK}			0.21		K/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) Min.	typ.	Max.	
I_S	V_{GS} = 0 V			80	A
I_{SM}	Repetitive			240	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %			1.5	V
T_{JM}	I_F = 25 A -di/dt = 100 A/µs		200		ns
Q_{RM}	V_R = 100 V		2		µC

TO-3P (IXTQ) Outline



1 – GATE
2 – DRAIN (COLLECTOR)
3 – SOURCE (EMITTER)
4 – DRAIN (COLLECTOR)

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
øP	.126	.134	3.20	3.40
øP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,850,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6771478 B2

Fig. 1. Output Characteristics @ 25°C

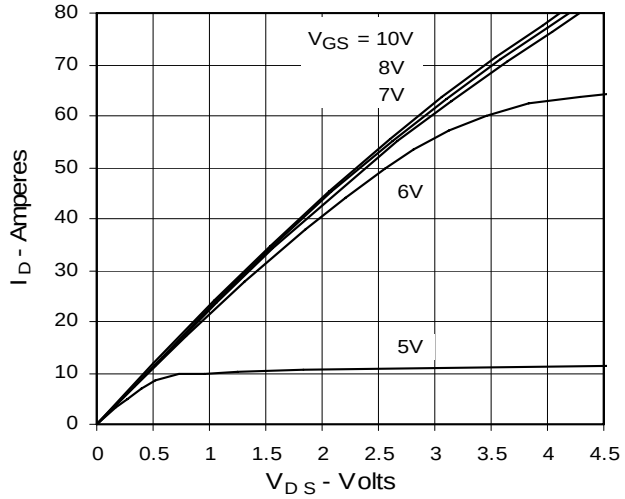


Fig. 2. Extended Output Characteristics @ 25°C

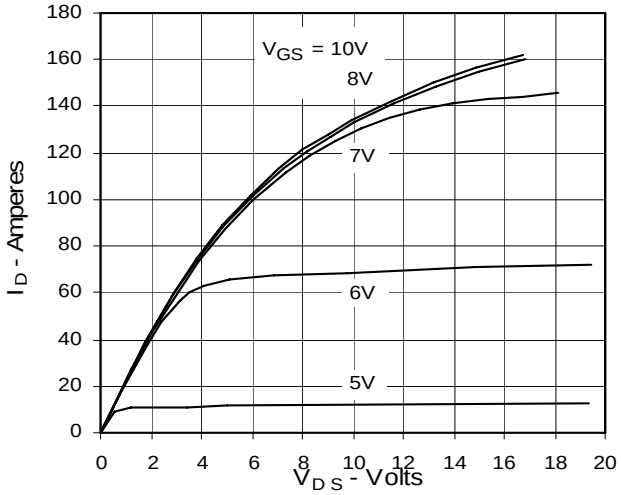


Fig. 3. Output Characteristics @ 125°C

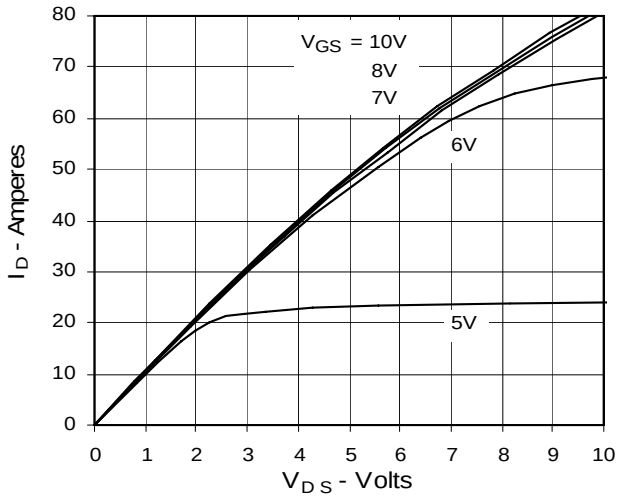


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

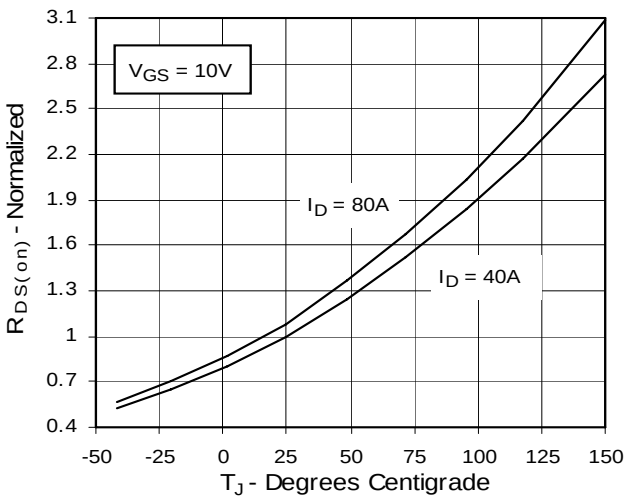


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

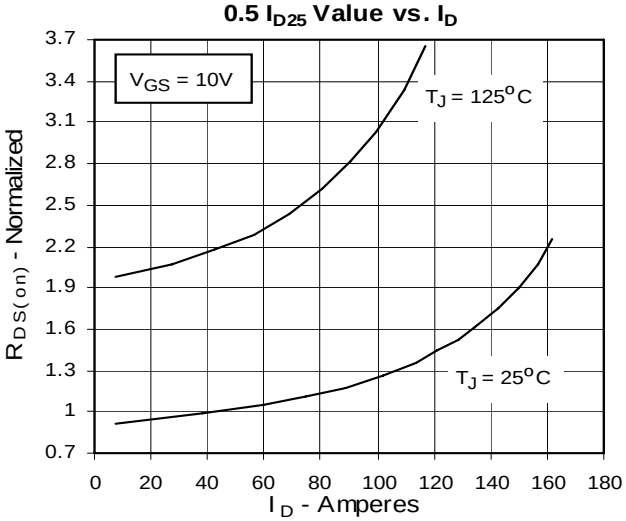
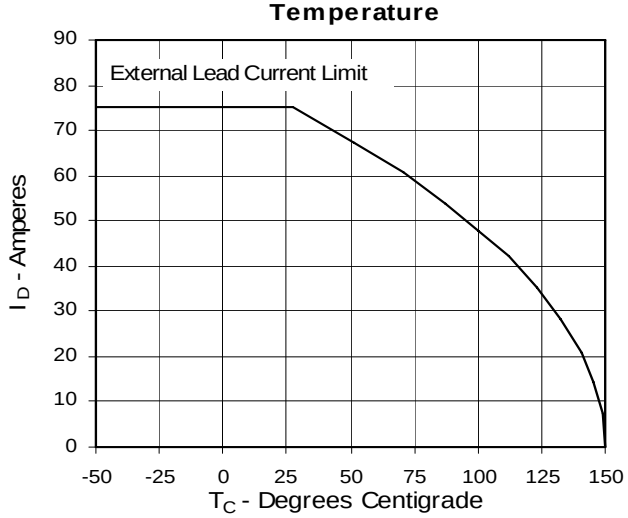


Fig. 6. Drain Current vs. Case Temperature



© 2006 IXYS All rights reserved

Fig. 7. Input Admittance

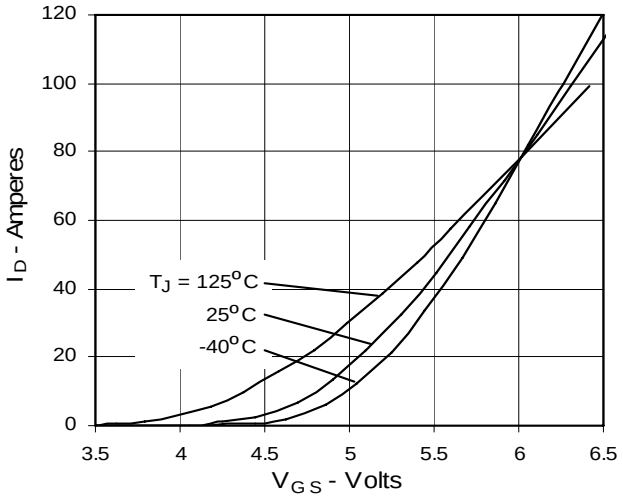


Fig. 8. Transconductance

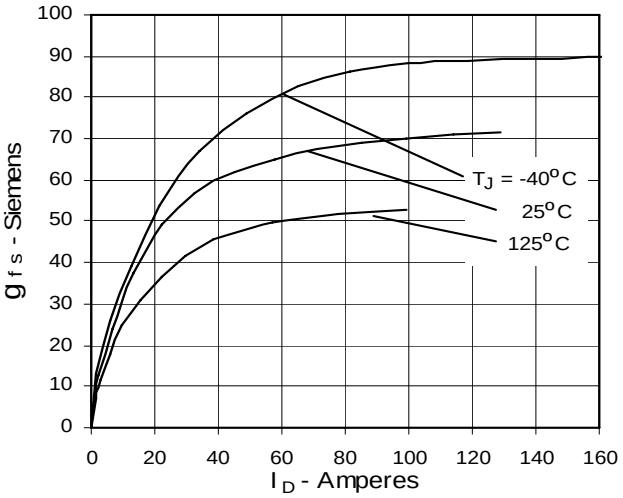


Fig. 9. Source Current vs. Source-To-Drain Voltage

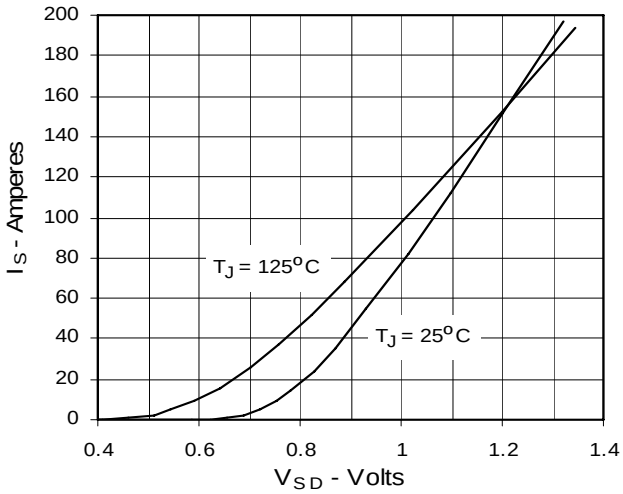


Fig. 10. Gate Charge

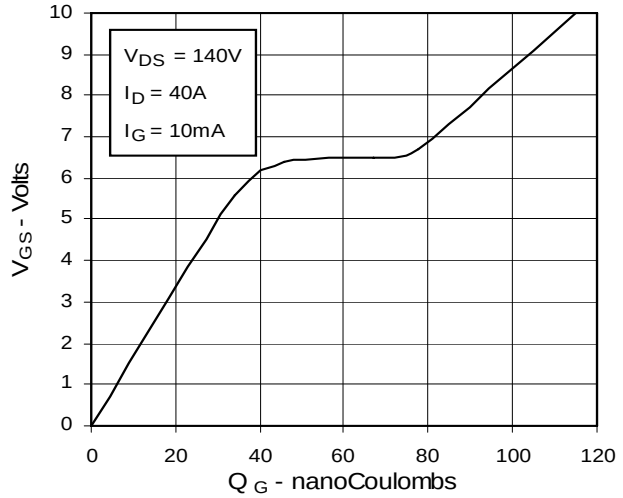


Fig. 11. Capacitance

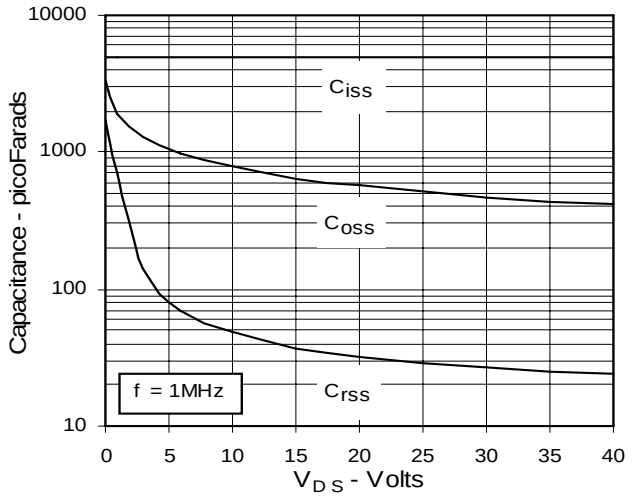
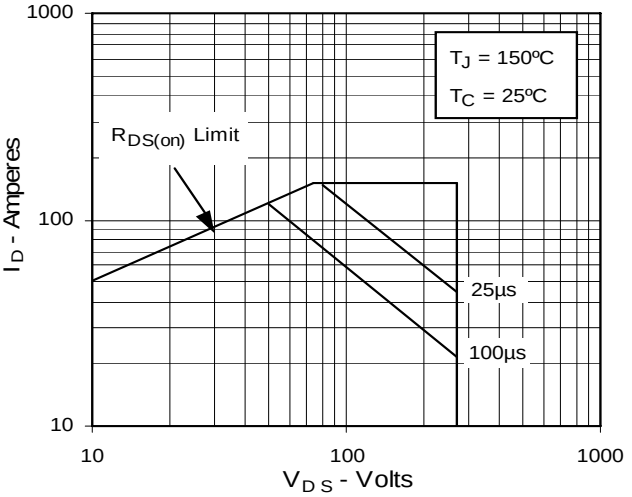
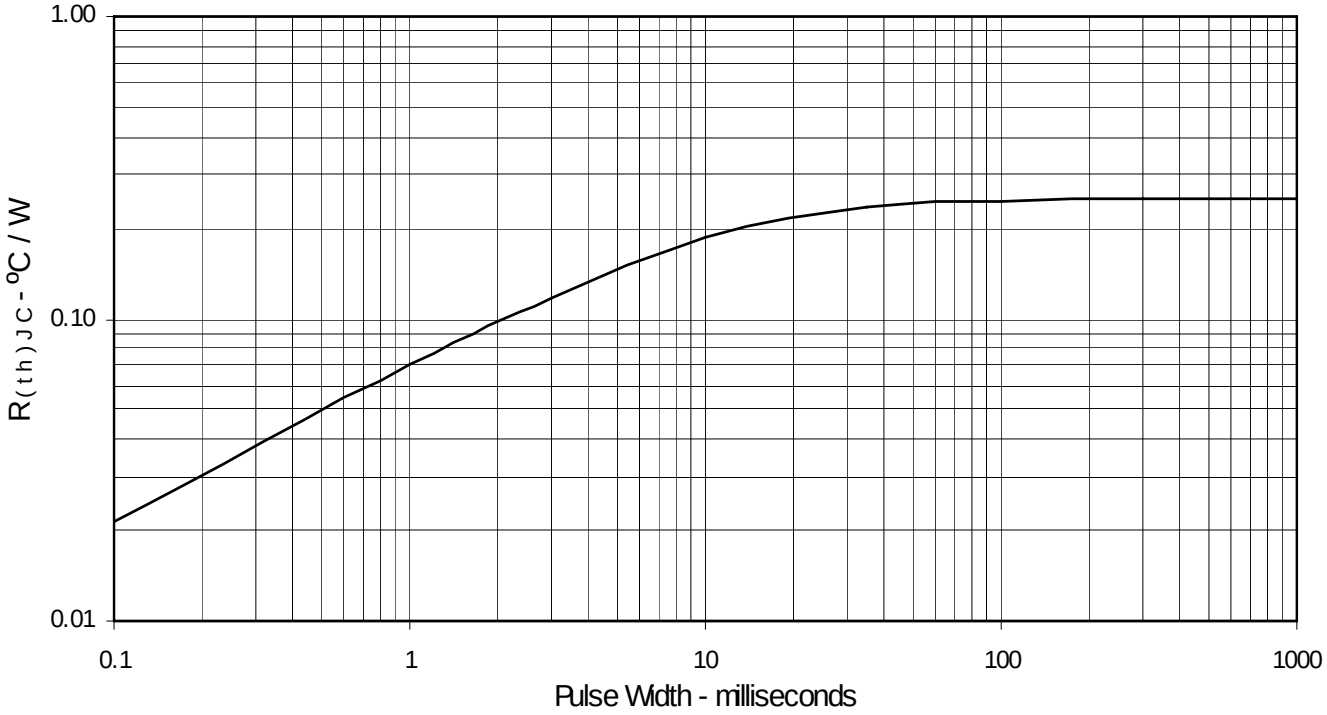


Fig. 12. Forward-Bias Safe Operating Area



IXYS reserves the right to change limits, test conditions, and dimensions.

Fig. 13. Maximum Transient Thermal Resistance



© 2006 IXYS All rights reserved